

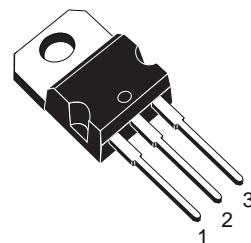

STP80N03L-06
**N - CHANNEL ENHANCEMENT MODE
"ULTRA HIGH DENSITY" POWER MOS TRANSISTOR**
TENTATIVE DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP80N03L-06	30 V	< 0.006 Ω	80 A (*)

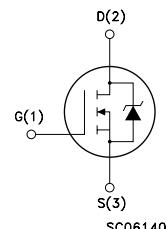
- TYPICAL R_{DS(on)} = 0.005 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE
- HIGH dV/dt RUGGEDNESS
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- POWER MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS
- SYNCRONOUS RECTIFICATION



TO-220

INTERNAL SCHEMATIC DIAGRAM


SC06140

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate-source Voltage	± 15	V
I _D	Drain Current (continuous) at T _c = 25 °C	80	A
I _D	Drain Current (continuous) at T _c = 100 °C	60	A
I _{DM(•)}	Drain Current (pulsed)	320	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	W
	Derating Factor	1	W/°C
dV/dt ₍₁₎	Peak Diode Recovery voltage slope	5	V/ns
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

STP80N03L-06

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	60	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	600	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	150	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	60	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 15 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1		2.5	V
R _{D(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 40 A V _{GS} = 10V I _D = 40 A T _c = 100°C V _{GS} = 5V I _D = 40 A V _{GS} = 5V I _D = 40 A T _c = 100°C		0.005 0.006	0.006 0.009	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{D(on)max} V _{GS} = 10 V	80			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{D(on)max} I _D = 10 A		35		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		6000 1000 250		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = V$ $I_D = A$ $R_G = \Omega$ $V_{GS} = V$ (see test circuit, figure 3)				ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = V$ $I_D = A$ $R_G = \Omega$ $V_{GS} = V$ (see test circuit, figure 5)				A/ μ s
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = V$ $I_D = A$ $V_{GS} = V$				nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(loff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = V$ $I_D = A$ $R_G = \Omega$ $V_{GS} = V$ (see test circuit, figure 5)				ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				80 320	A A
V_{SD} (*)	Forward On Voltage	$I_{SD} = A$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = A$ $di/dt = A/\mu$ s $V_{DD} = V$ $T_j = {}^\circ$ C (see test circuit, figure 5)				ns μ C A

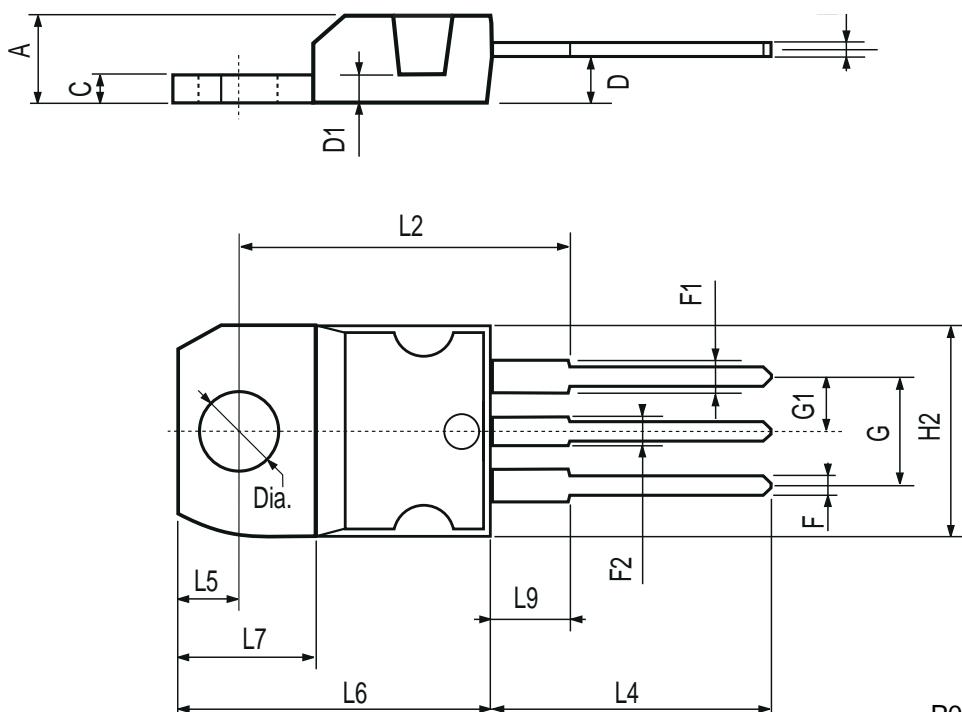
(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(*) Pulse width limited by safe operating area

(1) $I_{SD} \leq 60$ A, $di/dt \leq 200$ A/ μ s, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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